

Technical Data Data Sheet 4947, Rev. A

SILICON SCHOTTKY RECTIFIER DIE Very Low Forward Voltage Drop (150 °C T_J Operation)

Applications:

• Switching Power Supply • Converters • Free-Wheeling Diodes • Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Very Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics
- Electrically / Mechanically Stable during and after Packaging

Maximum Ratings⁽¹⁾:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	60	V
Max. Average Forward	I _{F(AV)}	50% duty cycle, rectangular	3	Α
Current	, ,	wave form		
Max. Peak One Cycle Non-	I _{FSM}	8.3 ms, half Sine wave (1)	55	Α
Repetitive Surge Current				
Non-Repetitive Avalanche	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 1.3 \text{A},$	8.6	mJ
Energy		L = 10 mH		
Repetitive Avalanche Current	I _{AR}	I _{AS} decay linearly to 0 in 1 μs	1.3	Α
		f limited by T _J max V _A =1.5V _R		
Max. Junction Temperature	TJ	-	-65 to +150	°C
Max. Storage Temperature	T_{stg}	-	-65 to +150	°C

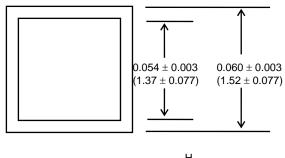
Electrical Characteristics(1):

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V _{F1}	@ 3A, Pulse, T _J = 25 °C	0.60	V
	V_{F2}	@ 3A, Pulse, T _J = 125 °C	0.55	V
Max. Reverse Current	I _{R1}	@V _R = 60V, Pulse,	400	μΑ
		T _J = 25 °C		
	I _{R2}	@V _R = 60V, Pulse,	28	mA
		T _J = 125 °C		
Max. Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 ^{\circ}C$	160	pF
		$f_{SIG} = 1MHz,$		
		$V_{SIG} = 50 \text{mV (p-p)}$		

(1) in SHD package

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Mechanical Dimensions: In Inches / mm



Bottom side metalization Ag - 30 kÅ minimum.

Top side metalization Al - 25 kÅ minimum or Ag - 30 kÅ minimum.

Bottom side is cathode, top side is anode.

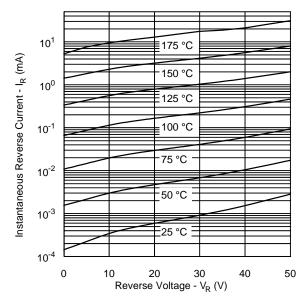
Dimension H = 0.0105 \pm 0.001 (0.27 \pm 0.026) for Al top; Dimension H = 0.0155 \pm 0.001 (0.39 \pm 0.026) for Ag top.



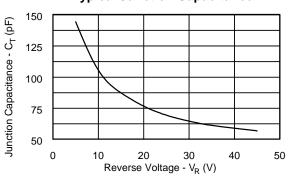
Typical Forward Characteristics

10¹ 175 °C 125 °C 10⁰ 125 °

Typical Reverse Characteristics



Typical Junction Capacitance





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